

## isc Silicon NPN Pow Transistor

2SC2482

## DESCRIPTION

- High breakdown voltage
- Low output capacitance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

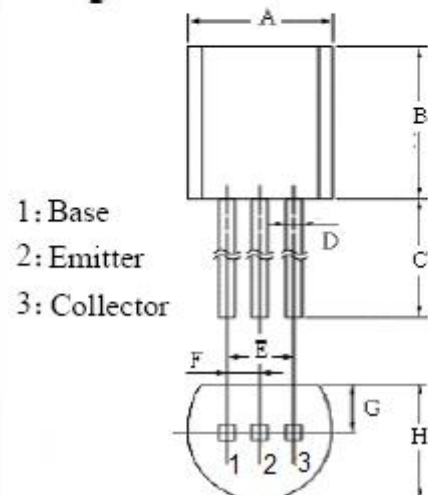
## APPLICATIONS

- Color TV chroma output applications
- Color TV horiz. driver applications
- High voltage switching and amplifier applications

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	300	V
$V_{CEO}$	Collector-Emitter Voltage	300	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current-Continuous	0.1	A
$P_C$	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	0.9	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$

TO-92 package



DIM	mm	
	MIN	MAX
A	4.33	4.83
B	4.33	4.83
C	14.0	15.0
D	0.36	0.56
E	2.54	
F	1.27	
G	0.92	1.12
H	3.40	3.60

**isc Silicon NPN Pow Transistor****2SC2482****ELECTRICAL CHARACTERISTICS****T<sub>c</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10mA ; I <sub>B</sub> = 1mA			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> =10mA ; I <sub>B</sub> = 1mA			1.0	V
I <sub>CB0</sub>	Collector Cutoff Current	V <sub>CB</sub> = 240V; I <sub>E</sub> = 0			1	μ A
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 20mA ; V <sub>CE</sub> = 10V	30		150	
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 20mA ; V <sub>CE</sub> = 10V		50		MHz